

STTB506B(-TR)

TURBOSWITCH™ "B". ULTRA-FAST HIGH VOLTAGE DIODE

MAIN PRODUCT CHARACTERISTICS

I _{F(AV)}	5 A
V _{RRM}	600 V
V _F (max)	1.3 V
t _{rr} (typ)	45 ns

FEATURES AND BENEFITS

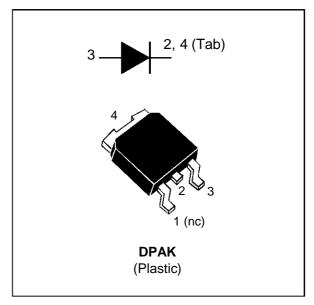
- SPECIFIC TO THE FOLLOWING OPERATIONS: SNUBBING OR CLAMPING, DEMAGNETIZA-TION AND RECTIFICATION, FREEWHEEL OR BOOSTER DIODE
- ULTRA-FAST RECOVERY
- VERY LOW OVERALL POWER LOSSES IN BOTH THE DIODE AND THE COMPANION TRANSISTOR
- DESIGNED FOR HIGH PULSED CURRENT OP-ERATIONS
- SURFACE MOUNT DEVICE
- TAPE AND REEL OPTION: -TR

DESCRIPTION

The TURBOSWITCH is a very high performance series of ultra-fast voltage power diodes from 600V to 1200V.

TURBOSWITCH "B" family drastically cuts losses in all high voltage operations which require extremely fast, soft and noise-free power diodes. They are particulary suitable in the primary circuit

PRELIMINARY DATASHEET



of an SMPS as snubber, clamping or demagnetizer diodes, and also in most power converters as high performance Rectifier diodes.

Packaged in DPAK Surface Mount enveloppe, these 600V devices are particulary intended for use on 240V domestic mains.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	600	V
V _{RSM}	Non Repetitive Surge Reverse Voltage	600	V
I _{F(RMS)}	RMS Forward Current	8	Α
I _{FRM}	Repetitive Peak Forward Current	65	А
T _{stg}	Storage Temperature Range	- 65 to + 150	°C
Tj	Max. Junction Temperature	150	°C

TM: TURBOSWITCH is a trademark from SGS-THOMSON Microelectronics.

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THERMAL AND POWER DATA

Symbol	Parameter	Conditions	Value	Unit
R _{th (j-c)}	Junction to Case Thermal Resistance		TBD	°C/W
P ₁	Conduction Power Dissipation	$I_{F(AV)} = 1.5A, \delta = 0.5$ $T_L = {}^{\circ}C$	TBD	W
P _{max}	Total Power Dissipation $P_{max} = P_1 + P_3$ $(P_3 = 10\% P_1)$	T _L = 76°C	TBD	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions	Tests	Min.	Тур.	Max.	Unit	
I _R *	Reverse leakage	Tj = 25°C	$V_R = 0.8 \times V_{RRM}$			100	μΑ
	Current	Tj = 125°C				0.75	mA
V _F **	Forward Voltage	Tj = 25°C	I _F = 5 A			1.4	V
	drop	Tj = 125°C	I _F = 5 A			1.3	

DYNAMIC ELECTRICAL CHARACTERISTICS

TURN-OFF SWITCHING

Symbol	Parameter		Test Conditions	Min.	Тур.	Max.	Unit
t _{rr}	Reverse Recovery Time	Tj = 25°C	I_F =0.5A I_R =1A I_{rr} =0.25A I_F =1A dI_F/dt =-50A/ μ s V_R =30V		45	95	ns
t _{fr}	Maximum Reverse Recovery Current	Tj = 125°C	$I_F=5A$ $V_R=400V$ $dI_F/dt = -40A/\mu s$ $dI_F/dt = -500A/\mu s$		20	7.5	А
S factor	Softness Factor	Tj = 125°C	V _R =400V I _F =5A dI _F /dt = -500A/μs		1		/

TURN-ON SWITCHING

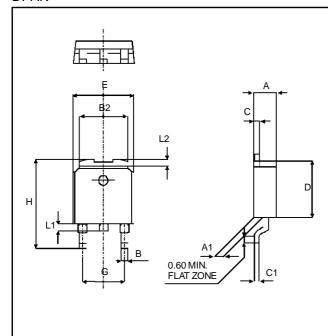
Symbol	Parameter	Test Conditions			Тур.	Max.	Unit
t _{rr}	Forward Recovery Time	Tj = 25°C	I_F =5A $dI_F/dt = 40A/\mu s$ Measured at 1.1 x V_{Fmax}			500	ns
V _{PF}	Peak Forward Voltage	Tj = 25°C	I _F =5A dI _F /dt = 40A/μs I _F =25A dI _F /dt=500A/μs		10	8	V



Pulse test: * tp = 5 ms, duty cycle < 2 %

^{**} tp = $380 \,\mu\text{s}$, duty cycle < 2%

PACKAGE MECHANICAL DATA DPAK



	DIMENSIONS						
REF.	Millimeters			Inches			
	Min.	Тур.	Max	Min.	Тур.	Max.	
Α	2.20		2.40	0.086		0.094	
A1	0.90		1.10	0.035		0.043	
В	0.64		0.90	0.025		0.035	
B2	5.20		5.40	0.204		0.212	
С	0.45		0.60	0.017		0.023	
C1	0.48		0.60	0.018		0.023	
D	6.00		6.20	0.236		0.244	
Е	6.40		6.60	0.251		0.259	
G	4.40		4.60	0.173		0.181	
Н	9.35		10.10	0.368		0.397	
L1	0.60		1.00	0.023		0.039	
L2		0.80			0.031		

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